



Dual P-Channel 1.8 V (G-S) MOSFET

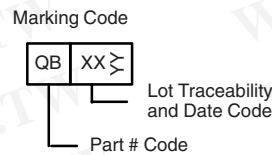
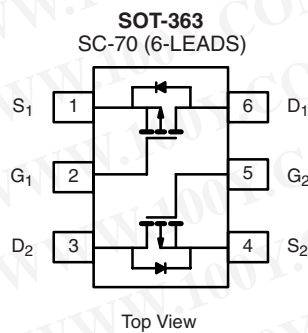
PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
- 8	0.600 at V _{GS} = - 4.5 V	± 0.60
	0.850 at V _{GS} = - 2.5 V	± 0.50
	1.200 at V _{GS} = - 1.8 V	± 0.42

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC



RoHS
 COMPLIANT
 HALOGEN
FREE
 Available



Ordering Information: Si1905DL-T1-E3 (Lead (Pb)-free)
 Si1905DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 8		V	
Gate-Source Voltage	V _{GS}	± 8			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	± 0.60	± 0.57	A
		T _A = 85 °C	± 0.43	± 0.41	
Pulsed Drain Current	I _{DM}	± 1.0			
Continuous Diode Current (Diode Conduction) ^a	I _S	- 0.25	- 0.23		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	0.30	0.27	W
		T _A = 85 °C	0.16	0.14	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	360	415	°C/W
	Steady State		400	460	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	300	350	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

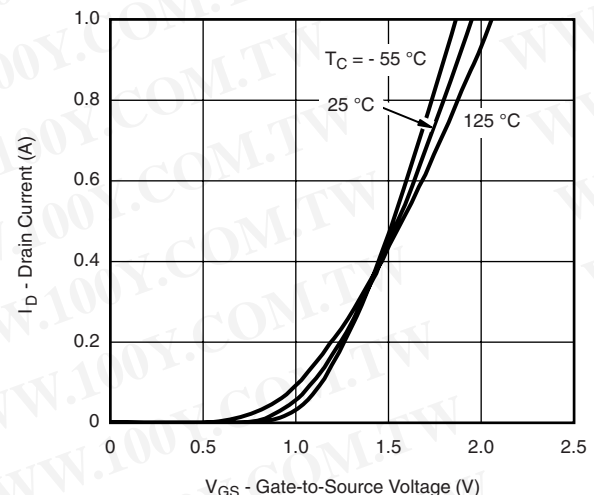
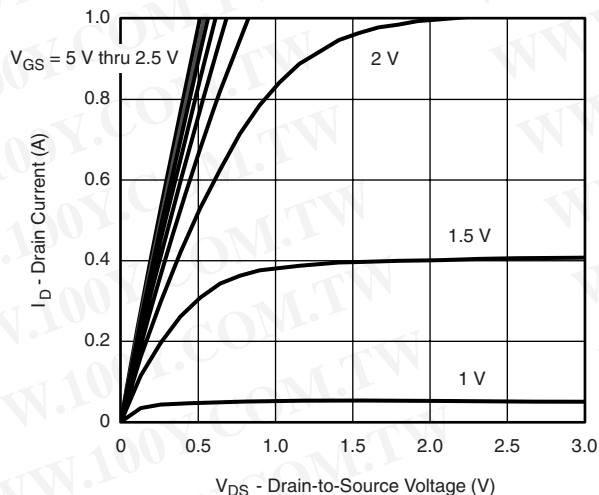
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -6.4\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -6.4\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-1.0			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -0.57\text{ A}$		0.51	0.600	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -0.48\text{ A}$		0.720	0.850	
		$V_{GS} = -1.8\text{ V}, I_D = -0.20\text{ A}$		1.0	1.200	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -0.57\text{ A}$		1.2		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.23\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -0.57\text{ A}$		1.5	2.3	nC
Gate-Source Charge	Q_{gs}		0.17			
Gate-Drain Charge	Q_{gd}		0.16			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 8\text{ }\Omega$ $I_D = -0.5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		6	12	ns
Rise Time	t_r		25	50		
Turn-Off Delay Time	$t_{d(off)}$		10	20		
Fall Time	t_f		10	20		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -0.23\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		20	40	

Notes:

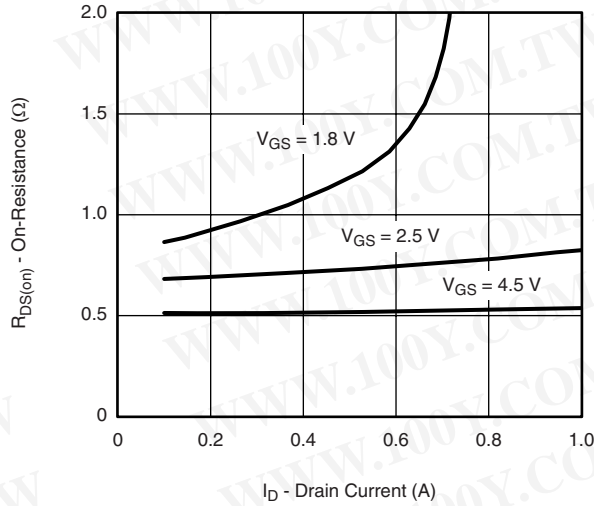
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

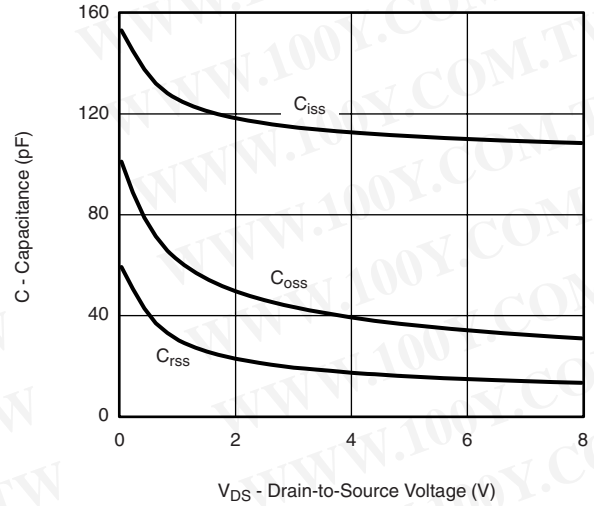
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



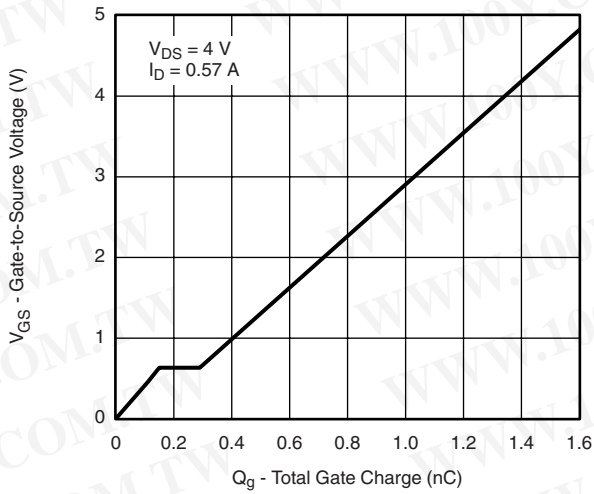
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



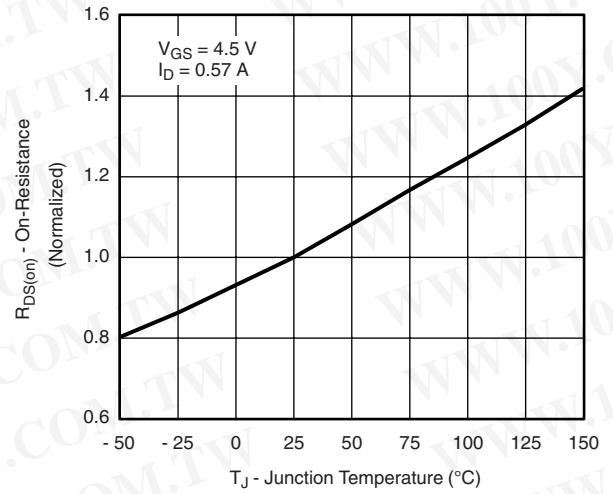
On-Resistance vs. Drain Current



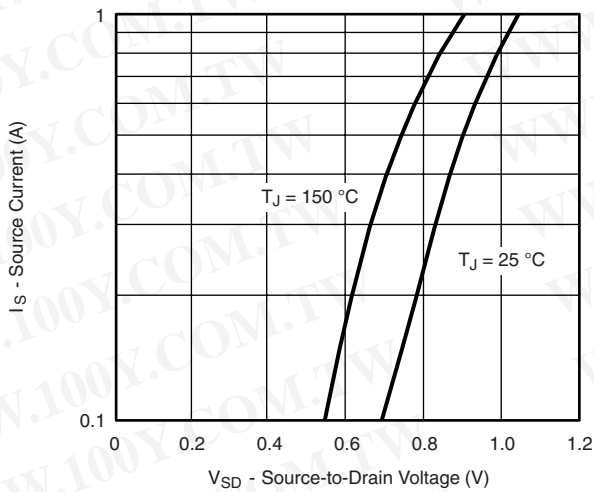
Capacitance



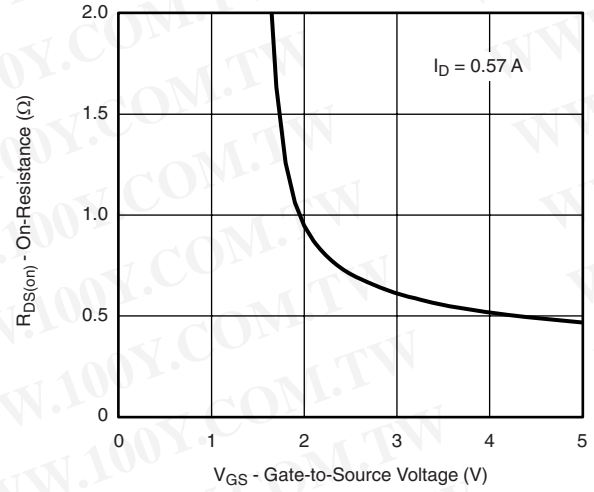
Gate Charge



On-Resistance vs. Junction Temperature



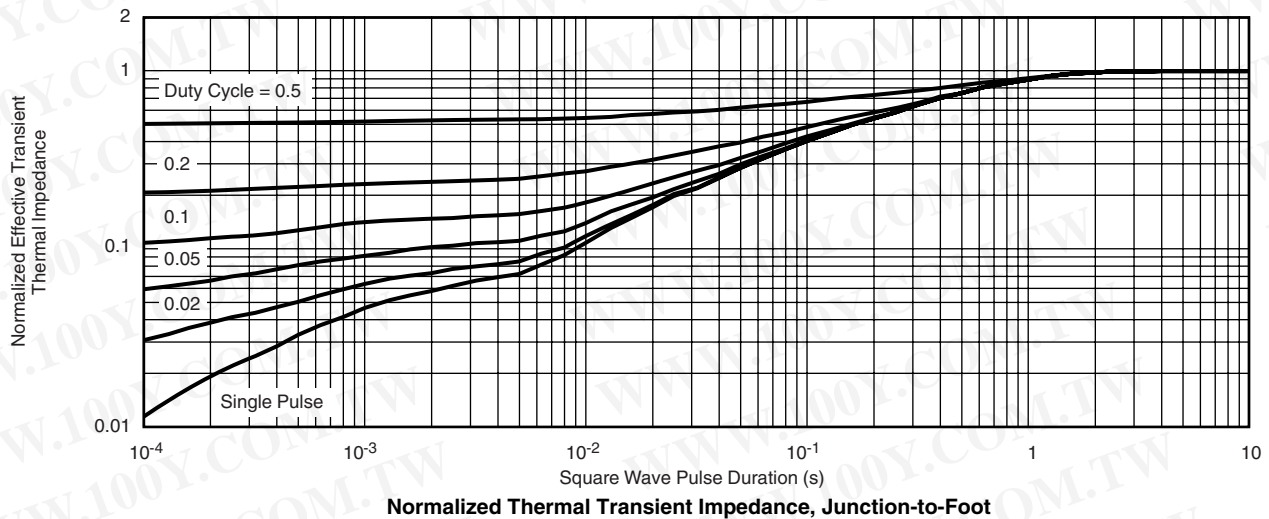
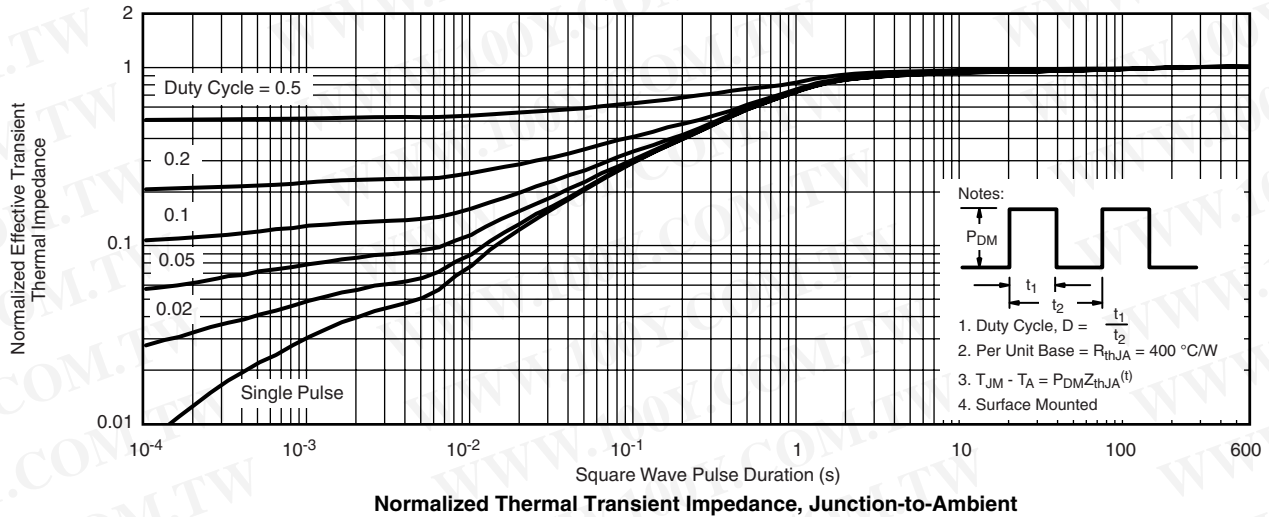
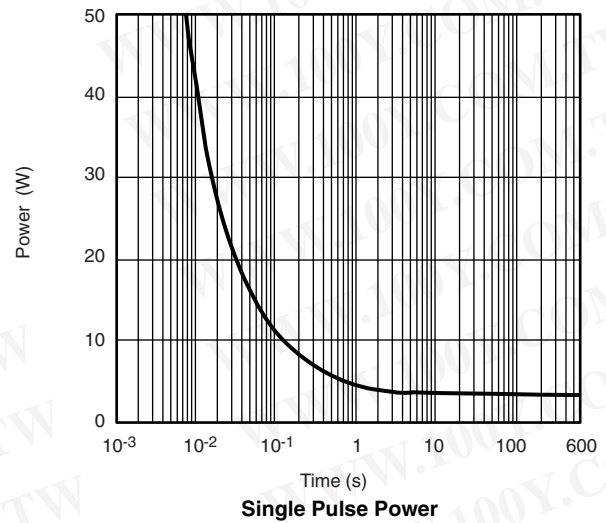
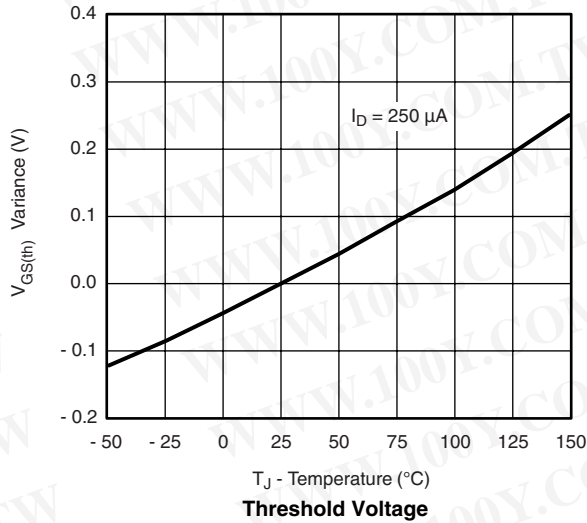
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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